

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"20020113959".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:32
S2	28	(uda-mitsuru\$ or kazunari-terakawa\$ or akira-suzuki\$).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 11:04
S3	19	(uda-mitsuru\$ or kazunari-terakawa\$ or akira-suzuki\$).in. and (semiconductor or wafer or resist\$ or reticl\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 11:04
S4	12	(uda-mitsuru\$ or kazunari-terakawa\$ or akira-suzuki\$).in. and (semiconductor or wafer or resist\$ or reticl\$) and angl\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:28
S5	2	(uda-mitsuru\$ or kazunari-terakawa\$ or akira-suzuki\$).in. and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ with "45")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 11:42
S6	16	"356"/\$.ccls. and (angl\$ with "45" with less).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:06
S7	15	"356"/\$.ccls. and (angl\$ with ("45" near6 less)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:03
S8	11	"356"/\$.ccls. and (angl\$ with ("45" near6 less)).clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:04
S9	9	"250"/\$.ccls. and (angl\$ with ("45" near6 less)).clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:05
S10	6	"250"/\$.ccls. and (angl\$ with ("45" near6 less)).clm. not "356"/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:05

S11	2	"356"/\$.ccls. and (angl\$ with "45" with less).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:07
S12	205	"356"/\$.ccls. and diffract\$.ab. and (fiber\$ or fibre\$) and (semiconductor or wafer or resist\$ or reticl\$) and angl\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 12:29
S13	152	"356"/\$.ccls. and diffract\$.ab. and (fiber\$ or fibre\$) and (semiconductor or wafer or resist\$ or reticl\$) and angl\$	USPAT	OR	ON	2004/12/06 12:30
S14	24	"356"/328.ccls. and diffract\$.ab. and (fiber\$ or fibre\$) and (semiconductor or wafer or resist\$ or reticl\$) and angl\$	USPAT	OR	ON	2004/12/06 12:32
S15	2	"356"/328.ccls. and diffract\$.ab. and (fiber\$ or fibre\$) and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ near8 less)	USPAT	OR	ON	2004/12/06 12:32
S16	8	"356"/328.ccls. and diffract\$.ab. and (fiber\$ or fibre\$) and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ near8 (less or maxim\$ or minim\$ or thresh\$))	USPAT	OR	ON	2004/12/06 12:34
S17	10	"356"/237.4,237.5.ccls. and diffract\$ and (fiber\$ or fibre\$) and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ near8 (less or maxim\$ or minim\$ or thresh\$))	USPAT	OR	ON	2004/12/06 12:44
S18	24	"356"/237.4,237.5.ccls. and diffract\$ and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ near8 (less or maxim\$ or minim\$ or thresh\$)) not (fiber\$ or fibre\$)	USPAT	OR	ON	2004/12/06 12:46
S19	2	"356"/237.4,237.5.ccls. and diffract\$ and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ near8 (less or maxim\$ or minim\$ or thresh\$)).ab. not (fiber\$ or fibre\$)	USPAT	OR	ON	2004/12/06 14:33
S20	16	"356"/237.4,237.5.ccls. and (diffract\$ near6 order\$) and (semiconductor or wafer or resist\$ or reticl\$) and (angl\$ near8 (less or maxim\$ or minim\$ or thresh\$))	USPAT	OR	ON	2004/12/06 14:34

S21	1220	"356"/\$.ccls. and (diffract\$.ab. or diffract\$.ti.) and (semiconductor or wafer or resist or reticle or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:36
S22	13	"356"/342.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:38
S23	34	"356"/636.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:42
S24	156	"356"/237.2.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:43
S25	37	"356"/237.2.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and (angl\$ near8 (less or maxim\$ or minim\$ or thresh\$))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:55
S26	97	"356"/\$.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and ((fiber\$ or fibre\$) same diverg\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:56
S27	63	"356"/\$.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and ((fiber\$ or fibre\$) same diverg\$) and (fiber\$ or fibre\$).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:57
S28	48	"356"/\$.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and ((fiber\$ or fibre\$) same diverg\$) and (fiber\$ or fibre\$).clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:58
S29	48	"356"/\$.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and ((fiber\$ or fibre\$) same diverg\$) and (fiber\$ or fibre\$).clm.	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:06
S30	265	"356"/237.2-237.5.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:06

S31	41	"356"/237.2-237.5.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and diverg\$	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:07
S32	38	"356"/237.2-237.5.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) and (diverg\$ same (light\$ or beam))	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:23
S33	227	"356"/237.2-237.5.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) not (diverg\$ same (light\$ or beam))	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:24
S34	9	"356"/237.2-237.5.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask) not (diverg\$ same (light\$ or beam)) and minus\$	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:29
S35	145	"356"/\$.ccls. and diffract\$ and back\$scatter\$ and (semiconductor or wafer or resist or reticle or mask)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:48
S36	3117	"356"/\$.ccls. and diffract\$ and (semiconductor or wafer or resist or reticle or mask)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:48
S37	1163	"356"/\$.ccls. and diffract\$.clm. and (semiconductor or wafer or resist or reticle or mask)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:55
S38	0	"356"/\$.ccls. and diffract\$.clm. and (semiconductor or wafer or resist or reticle or mask) and "visual\$.clm"	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:49
S39	36	"356"/\$.ccls. and diffract\$.clm. and (semiconductor or wafer or resist or reticle or mask) and visual\$.clm.	USPAT; EPO; IBM_TDB	OR	ON	2004/12/06 17:49
S40	1	"6825924".pn.	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:03
S41	310	shallow same ("45" near6 degree)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:03
S42	70	shallow with ("45" near6 degree)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:36
S43	1	"356"/\$.ccls. and (shallow with ("45" near6 degree))	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:04

S44	1	"250"/\$.ccls. and (shallow with ("45" near6 degree))	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:04
S45	349	(fibre\$ or fiber\$) with ("70" near6 degree)	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:37
S46	14	("356"/\$ or "250"/\$).ccls. and ((fibre\$ or fiber\$) with ("70" near6 degree))	USPAT; EPO; IBM_TDB	OR	ON	2004/12/07 14:37